

UCS-4401H AND UCS-4801H HERMETIC BiMOS LATCHED DRIVERS

MIL-STD-883 Compliant

FEATURES

- High-Voltage, High-Current Outputs
- Output Transient Protection
- CMOS, PMOS, NMOS, TTL Compatible
- Internal Pull-Down Resistors
- Low-Power CMOS Latches
- High-Reliability Screening to MIL-STD-883, Class B

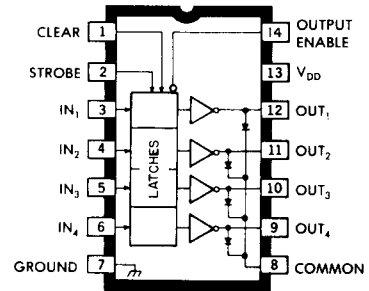
HIGH-VOLTAGE, HIGH-CURRENT interface for military, aerospace and related applications is supplied by these latched drivers. Type UCS-4401H contains four pairs of latches and drivers; Type UCS-4801H has eight pairs of latches and drivers.

The integrated circuits' CMOS inputs work with standard CMOS, PMOS and NMOS logic levels and (with appropriate pull-up resistors) with TTL or DTL circuits. The bipolar open-collector outputs can be used with relays, solenoids, motors, LED or incandescent displays, and other high-power loads.

The output transistors can sink 500 mA and will withstand a V_{CE} of 50 V in the OFF state. Outputs can be paralleled for higher current capability. Because of limitations on package power dissipation, simultaneous operation of all drivers at maximum rated current can only be accomplished with a reduction of duty cycle.

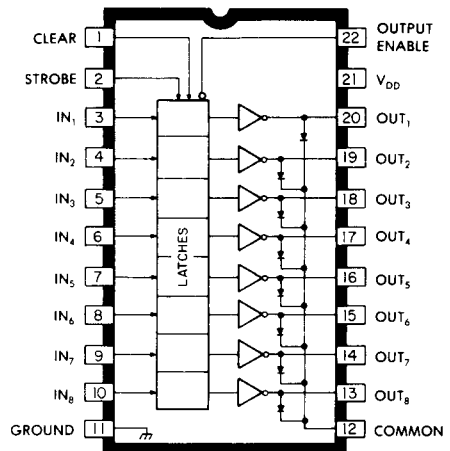
Type UCS-4401H, the four-latch device, is furnished in a standard 14-pin side-brazed hermetic package. Type UCS-4801H, the eight-latch device, is furnished in a 22-pin side-brazed hermetic package with row centers 0.400-inch (10.16 mm) apart.

Monolithic construction enables cost-effective and reliable systems design. Reverse-bias burn-in and 100% high-reliability screening to MIL-STD-883, Class B are standard.



Dwg. No. A-10.499B

UCS-4401H



Dwg. No. A-10.498B

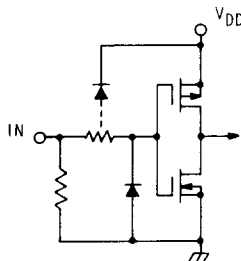
UCS-4801H

ABSOLUTE MAXIMUM RATINGS

Output Voltage, V_{CE}	50 V
Supply Voltage, V_{DD}	18 V
Input Voltage Range, V_{IN}	- 0.3 V to $V_{DD} + 0.3$ V
Continuous Collector Current, I_C	500 mA
Package Power Dissipation, P_D	See Graph
Operating Ambient Temperature Range, T_A	- 55°C to + 125°C
Storage Temperature Range, T_S	- 65°C to + 150°C

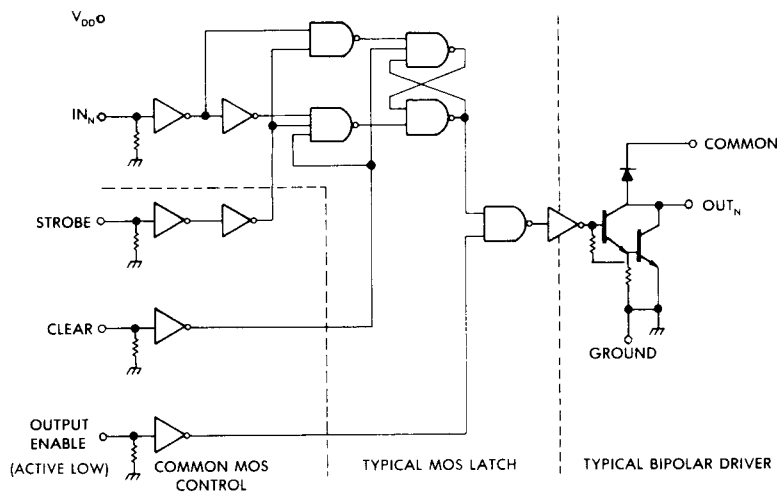
CAUTION: Sprague CMOS devices have input static protection but are susceptible to damage when exposed to extremely high static electrical charges.

TYPICAL INPUT CIRCUIT



Dwg. No. A-12.520

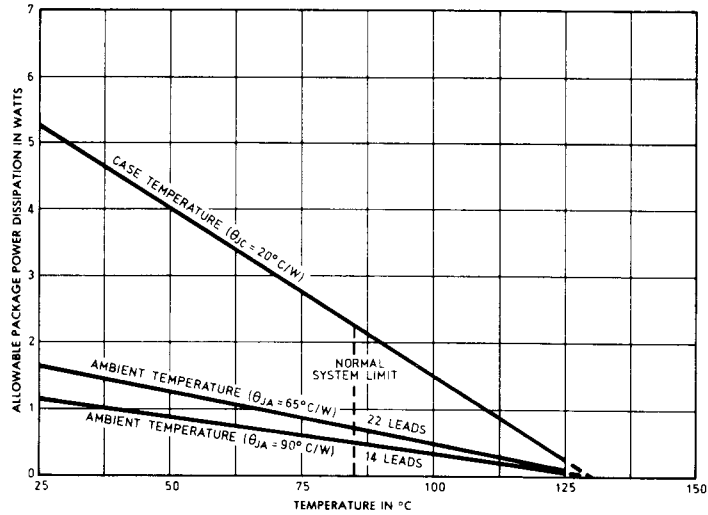
FUNCTIONAL BLOCK DIAGRAM



Dwg. No. A-10.495B

**UCS-4401H AND UCS-4801H
HERMETIC BiMOS LATCHED DRIVERS**

**ALLOWABLE AVERAGE PACKAGE POWER DISSIPATION
AS A FUNCTION OF TEMPERATURE**



Dwg. No. A-11.464

ELECTRICAL CHARACTERISTICS at $T_A = +25^\circ\text{C}$, $V_{DD} = 5\text{ V}$ (unless otherwise specified)

Characteristic	Symbol	Test Conditions	Limits			
			Min.	Typ.	Max.	Units
Output Leakage Current	I_{CEX}	$V_{CE} = 50\text{ V}$	—	—	50	μA
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = 100\text{ mA}$	—	0.9	1.1	V
		$I_C = 200\text{ mA}$	—	1.1	1.3	V
		$I_C = 350\text{ mA}$, $V_{DD} = 7.0\text{ V}$	—	1.3	1.6	V
Input Voltage	$V_{IN(0)}$ $V_{IN(1)}$	$V_{DD} = 15\text{ V}$	13.5	—	—	V
		$V_{DD} = 10\text{ V}$	8.5	—	—	V
		$V_{DD} = 5.0\text{ V}$ (See note)	3.5	—	—	V
Input Resistance	R_{IN}	$V_{DD} = 15\text{ V}$	50	200	—	$\text{k}\Omega$
		$V_{DD} = 10\text{ V}$	50	300	—	$\text{k}\Omega$
		$V_{DD} = 5.0\text{ V}$	50	600	—	$\text{k}\Omega$
Supply Current	$I_{DD(ON)}$ (Each stage)	$V_{DD} = 15\text{ V}$, Outputs Open	—	1.0	2.0	mA
		$V_{DD} = 10\text{ V}$, Outputs Open	—	0.9	1.7	mA
		$V_{DD} = 5.0\text{ V}$, Outputs Open	—	0.7	1.0	mA
	$I_{DD(OFF)}$	All Drivers OFF, $V_{IN} = 0\text{ V}$	—	50	100	μA
		All Drivers OFF, $V_{IN} = 0\text{ V}$, $V_{DD} = 15\text{ V}$	—	—	200	μA
Clamp Diode Leakage Current	I_R	$V_R = 50\text{ V}$	—	—	50	μA
Clamp Diode Forward Voltage	V_F	$I_F = 350\text{ mA}$	—	1.7	2.0	V

Note: Operation of these devices with standard TTL or DTL may require the use of appropriate pull-up resistors to insure the minimum logic "1".

ELECTRICAL CHARACTERISTICS at $T_A = -55^\circ\text{C}$, $V_{DD} = 5\text{ V}$ (unless otherwise specified)

Characteristic	Symbol	Test Conditions	Limits			
			Min.	Typ.	Max.	Units
Output Leakage Current	I_{CEX}	$V_{CE} = 50\text{ V}$	—	—	50	μA
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = 100\text{ mA}$	—	—	1.3	V
		$I_C = 200\text{ mA}$	—	—	1.5	V
		$I_C = 350\text{ mA}$, $V_{DD} = 7.0\text{ V}$	—	—	1.8	V
Input Voltage	$V_{IN(0)}$ $V_{IN(1)}$	$V_{DD} = 15\text{ V}$	14	—	—	V
		$V_{DD} = 10\text{ V}$	9.0	—	—	V
		$V_{DD} = 5.0\text{ V}$ (See note)	3.6	—	—	V
Input Resistance	R_{IN}	$V_{DD} = 15\text{ V}$	35	—	—	$\text{k}\Omega$
		$V_{DD} = 10\text{ V}$	35	—	—	$\text{k}\Omega$
		$V_{DD} = 5.0\text{ V}$	35	—	—	$\text{k}\Omega$
Supply Current	$I_{DD(ON)}$ (Each stage)	$V_{DD} = 15\text{ V}$, Outputs Open	—	1.0	2.5	mA
		$V_{DD} = 10\text{ V}$, Outputs Open	—	0.9	1.9	mA
		$V_{DD} = 5.0\text{ V}$, Outputs Open	—	0.7	1.2	mA
	$I_{DD(OFF)}$	All Drivers OFF, $V_{IN} = 0\text{ V}$	—	50	100	μA
		All Drivers OFF, $V_{IN} = 0\text{ V}$, $V_{DD} = 15\text{ V}$	—	—	200	μA
Clamp Diode Leakage Current	I_R	$V_R = 50\text{ V}$	—	—	50	μA
Clamp Diode Forward Voltage	V_f	$I_f = 350\text{ mA}$	—	—	2.1	V

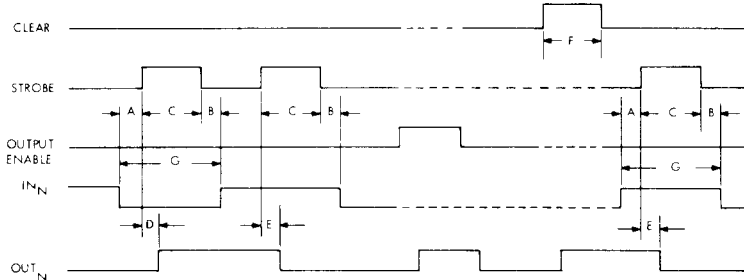
ELECTRICAL CHARACTERISTICS at $T_A = +125^\circ\text{C}$, $V_{DD} = 5\text{ V}$ (unless otherwise specified)

Characteristic	Symbol	Test Conditions	Limits			
			Min.	Typ.	Max.	Units
Output Leakage Current	I_{CEX}	$V_{CE} = 50\text{ V}$	—	—	500	μA
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = 100\text{ mA}^*$	—	—	1.3	V
		$I_C = 200\text{ mA}^*$	—	—	1.5	V
		$I_C = 350\text{ mA}$, $V_{DD} = 7.0\text{ V}^*$	—	—	1.8	V
Input Voltage	$V_{IN(0)}$ $V_{IN(1)}$	$V_{DD} = 15\text{ V}$	13.5	—	—	V
		$V_{DD} = 10\text{ V}$	8.5	—	—	V
		$V_{DD} = 5.0\text{ V}$ (See note)	3.5	—	—	V
Input Resistance	R_{IN}	$V_{DD} = 15\text{ V}$	50	—	—	$\text{k}\Omega$
		$V_{DD} = 10\text{ V}$	50	—	—	$\text{k}\Omega$
		$V_{DD} = 5.0\text{ V}$	50	—	—	$\text{k}\Omega$
Supply Current	$I_{DD(ON)}$ (Each stage)	$V_{DD} = 15\text{ V}$, Outputs Open	—	1.0	2.0	mA
		$V_{DD} = 10\text{ V}$, Outputs Open	—	0.9	1.7	mA
		$V_{DD} = 5.0\text{ V}$, Outputs Open	—	0.7	1.0	mA
	$I_{DD(OFF)}$	All Drivers OFF, $V_{IN} = 0\text{ V}$	—	50	100	μA
		All Drivers OFF, $V_{IN} = 0\text{ V}$, $V_{DD} = 15\text{ V}$	—	—	200	μA
Clamp Diode Leakage Current	I_R	$V_R = 50\text{ V}$	—	—	500	μA
Clamp Diode Forward Voltage	V_f	$I_f = 350\text{ mA}^*$	—	—	2.0	V

Note: Operation of these devices with standard TTL or DTL may require the use of appropriate pull-up resistors to insure the minimum logic '1'.
*Pulsed test.

TIMING CONDITIONS

$T_a = +25^\circ\text{C}$; Logic Levels are V_{cc} and Ground



Dwg No A-10.895A

- A. Minimum data active time before strobe enabled (data set-up time) 100 ns
- B. Minimum data active time after strobe disabled (data hold time) 100 ns
- C. Minimum strobe pulse width 300 ns
- D. Typical time between strobe activation and output on to off transition 500 ns
- E. Typical time between strobe activation and output off to on transition 500 ns
- F. Minimum clear pulse width 300 ns
- G. Minimum data pulse width 500 ns

Information present at an input is transferred to its latch when the STROBE is high. A high CLEAR input will set all latches to the output OFF condition regardless of the data or STROBE input levels. A high OUTPUT ENABLE will set all outputs to the OFF condition regardless of any other input conditions. When the OUTPUT ENABLE is low, the outputs depend on the state of their respective latches.

TRUTH TABLE

IN_n	STROBE	CLEAR	OUTPUT ENABLE	OUT_n	
				t-1	t
0	1	0	0	X	OFF
1	1	0	0	X	ON
X	X	1	X	X	OFF
X	X	X	1	X	OFF
X	0	0	0	ON	ON
X	0	0	0	OFF	OFF

X = irrelevant
t-1 = previous output state
t = present output state